RICOH

R1293K Series

Multi Power Supply IC with Amplifier for LCD

NO.EA-301-160107

OUTLINE

The R1293K is a multi power supply IC dedicated for mid-size TFT LCD panels. The R1293K consists of a PWM control step-up DC/DC converter, an LDO regulator, a VCOM amplifier and six GAMMA amplifiers. The output noise can be reduced by SEL pin. (SEL pin "H": normal mode, SEL pin "L": low noise mode.) The MOSFET for step-up DC/DC converter is built-in and, low power operation is realized by standby mode. The package is 4mm square QFN(PLP)0404-32.

FEATURES

Ste	-up DC/DC converter part
•	Input Voltage Range
•	Adjustable Output Voltage Range with external resistors up to 16V
•	Feedback Voltage

- Feedback Voltage Accuracy ±1.5%
- Adjustable Oscillator Frequency with external resistors for RT pin 300kHz to 1MHz
- Adjustable Phase compensation with external components
- Internal Soft Start TimeTYP. 10ms
- Adjustable Soft Start Time with external capacitors for DTC pin
- Oscillator Maximum Duty CycleSet with external resistors for DTC pin (Limit TYP. 90%)
- UVLO detector threshold--------TYP. 1.9V
- Internal 2A /16V capability Nch MOSFET Driver ······TYP. 0.2Ω
- Built-in Peak Current Limit Circuit
- Short Protection with timer latch function (Adjustable delay time with external capacitors for Delay pin)

LDO part

- Output Voltage Accuracy-----±1.0%
- Maximum Output CurrentMin. 350mA guaranteed
- Ripple Rejection TYP. 65db (Frequency = 1kHz)

Buffer Amplifier part

- Input Voltage Range for Amplifiers5V to 16V (VBUFF pin)
- Output Current Range for VCOM Amplifier.....-100mA

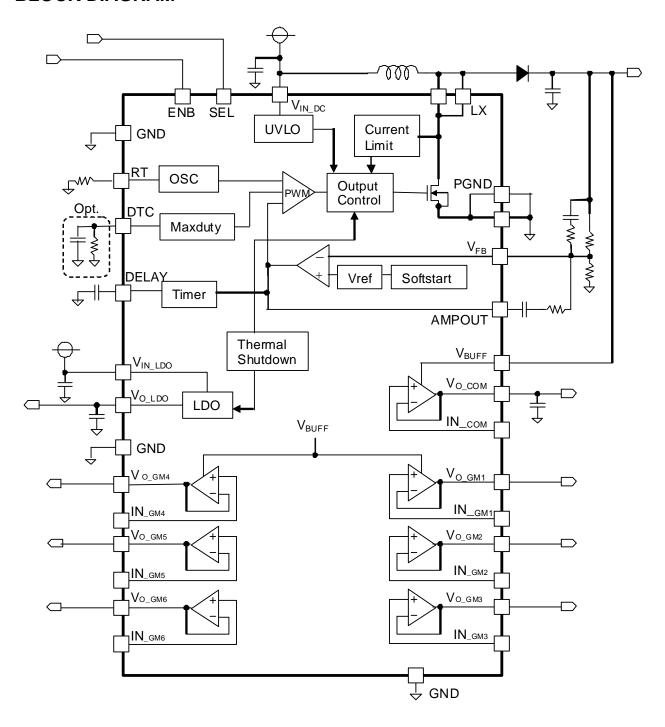
Others

- Built-in Thermal Shutdown Circuit
- Stand-by function by ENB pin

APPLICATIONS

Power sources of the medium and small sized TFT LCD panels

BLOCK DIAGRAM



R1293K Block Diagram

SELECTION GUIDE

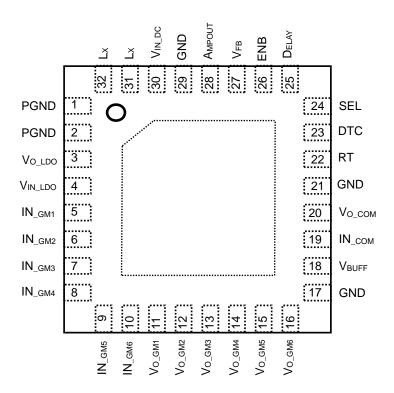
The output voltage (Vout) for the ICs is a user-selectabe option.

 V_{OUT} can be set within the range of 1.8 V to 2.5 V in 0.1 V steps.

Selection Guide

Product Name	oduct Name Package		Pb Free	Halogen Free					
R1293Kxx1A-E2	QFN(PLP)0404-32	2,000 pcs	Yes	Yes					
xx: Designation of the LDO output voltage (V _{OUT})									

PIN CONFIGURATION



QFN(PLP)0404-32 Pin Configuration

R1293K

NO.EA-301-160107

PIN DESCRIPTIONS

R1293K Pin Description

Pin No	Symbol	Description	Notes
1	PGND	Power GND Pin	Make the PGND pin a short-circuit with the GND pin.
2	PGND	Power GND Pin	Make the PGND pin a short-circuit with the GND pin.
3	Vo_ldo	LDO Output Pin	
4	VIN_LDO	LDO Power Input Pin	Input 2.2V to 5.5V to VIN_LDO. Make VIN_LDO a short-circuit with the VIN_DC pin.
5	IN_ _{GM1} *1	GAMMA1 Input Pin	
6	IN_ _{GM2} *1	GAMMA2 Input Pin	
7	IN_ _{GM3} *1	GAMMA3 Input Pin	
8	IN_ _{GM4} *1	GAMMA4 Input Pin	
9	IN_GM5 ^{*1}	GAMMA5 Input Pin	
10	IN_GM6 ^{*1}	GAMMA6 Input Pin	
11	Vo_gм1	GAMMA1 Output Pin	
12	Vo_gm2	GAMMA2 Output Pin	
13	Vo_Gмз	GAMMA3 Output Pin	
14	Vo_gm4	GAMMA4 Output Pin	
15	Vo_gm5	GAMMA5 Output Pin	
16	Vo_Gм6	GAMMA6 Output Pin	
17	GND	GND Pin	
18	VBUFF	Buffer Amplifier Power Source Pin	Connect the VBUFF pin to Boost Output.
19	IN_com ^{*1}	VCOM Input Pin	
20	Vo_сом	VCOM Output Pin	
21	GND	GND Pin	
22	RT	Oscillator Frequency Setting Pin	Connect a resistor to the RT pin to set the operation frequency.
23	DTC	Maxduty/ Soft-start Time Setting Pin	By adding a resistor, the Maxduty limit can be set; otherwise the Maxduty limit will be the preset value set inside the ICs. By adding a capacitor, Maxduty can start from 0 which means startup-time can be set longer.
24	SEL*1	Noise Reduction Level Selection Pin	"L" Input: Low Noise Mode "H" Input: Normal Mode

Pin No	Symbol	Description	Notes
25	DELAY	Short-circuit Protection Delay Time Setting Pin	By adding a capacitor, the DELAY pin can set a protection delay time.
26	ENB*1	Chip Enable Pin (DC/DC or Buffer Amplifier)	"L" Input: Active
27	V _{FB}	DC/ DC Feedback Pin	
28	AMPOUT	DC/ DC Phase Compensation Pin	
29	GND	GND Pin	
30	V _{IN_DC}	DC/ DC Power Source Pin	Input voltage should be 2.2V to 5.5V. Make the V _{IN_DC} pin a short-circuit with the V _{IN_LDO} pin.
31	Lx	DC/ DC Switching Pin	
32	Lx	DC/ DC Switching Pin	

The exposed tab on the bottom of the package enhances thermal performance and is electrically connected to GND(substrate level). It is recommended that the exposed tab be connected to the ground plane on the board otherwise be left open.

 $^{^{\}star 1}$ Do not leave the IN_GM1 to IN_GM6, IN_COM, SEL and ENB pins open.

ABSOLUTE MAXIMAM RATINGS

Absolute Maximum Ratings

(GND = PGND = 0 V)

Symbol	Item	Rating	$\frac{PGND = 0 \text{ V}}{\text{Unit}}$
VIN_DC	V _{IN_DC} Pin Voltage	-0.3 to 6.5	V
V _{IN_LDO}	V _{IN_LDO} Pin Voltage	-0.3 to 6.5	V
VBUFF	VBUFF Pin Voltage	-0.3 to 24	V
V _{RT}	RT Pin Voltage	-0.3 to 4.0	V
V _{DTC}	DTC Pin Voltage	-0.3 to 4.0	V
V _{FB}	V _{FB} Pin Voltage	-0.3 to 4.0	V
V _{AMP}	AMPOUT Pin Voltage	-0.3 to 4.0	V
VDELAY	DELAY Pin Voltage	-0.3 to 4.0	V
Vsel	SEL Pin Voltage	-0.3 to 6.5	V
VENB	ENB Pin Voltage	-0.3 to 6.5	V
VLX	Lx Pin Voltage	-0.3 to 24	V
Vo_ldo	Vo_LDO Pin Output Voltage	-0.3 to V _{IN_LDO} +0.3	V
lo_ldo	Vo_LDO Pin Output Current	450	mA
VIN_BUFF	Buffer Amplifier Input Voltage	-0.3 to VBUFF+0.3	V
Vo_buff	Buffer Amplifier Output Voltage	-0.3 to VBUFF+0.3	V
P _D	Power Dissipation (Standard Land Pattern)*1	1500	mW
Ta	Operating Temperature Range	-40 to +85	°C
Tstg	Storage Temperature Range	-55 to +125	°C
Tj	Junction Temperature	-40 to +125	°C

^{*1} For more information about the Power Dissipation, please refer to PACKAGE INFORMATION.

ABSOLUTE MAXIMUM RATINGS

Electronic and mechanical stress momentarily exceeded absolute maximum ratings may cause the permanent damages and may degrade the life time and safety for both device and system using the device in the field. The functional operation at or over these absolute maximum ratings is not assured.

RECOMMENDED OPERATING CONDITIONS (ELECTRICAL CHARACTERISTICS)

All of electronic equipment should be designed that the mounted semiconductor devices operate within the recommended operating conditions. The semiconductor devices cannot operate normally over the recommended operating conditions, even if when they are used over such conditions by momentary electronic noise or surge. And the semiconductor devices may receive serious damage when they continue to operate over the recommended operating conditions.

ELECTRICAL CHARACTERISTICS

 $V_{IN_DC} = 3.6 \text{ V}$, Ta = 25°C unless otherwise noted.

LDO Output Current Limit

LDO Short Current

R1293K Electrical Characteristics

Symbol	Item	Condi	itions	Min.	Тур.	Max.	Unit
Vin	V _{IN} Input Voltage	VIN = VIN_DC = VIN	2.2		5.5	V	
lin	V _{IN} Supply Current	VIN_DC=5.5V, VF		300	550	μA	
Іѕтв	Standby V _{IN} Current	VIN_DC=5.5V		60	90	μA	
V _{UVLO1}	UVLO Detector Threshold	V _{IN_DC} =2.2V→1.	7V	1.8	1.9	2.0	V
V _{UVLO2}	UVLO Release Voltage	V _{IN_DC} =1.7V→2		2.05	2.15	V	
DC/ DC CC	ONVERTER						
V_{FB}	V _{FB} Voltage			0.985	1.000	1.015	V
A٧	Opened-loop Voltage Grain				90		dB
f⊤	Single Gain-bandwidth Range	Av=0dB			1.8		MHz
I _{АМРН}	AMP "H" Output Current	Vamp=1V, Vfb=0.	.9V	0.3	1.4	3.5	mA
IAMPL	AMP "L" Output Current	Vamp=1V, Vfb=1.	.1V	50	90	150	μA
fosc	Oscillator Frequency	VDELAY=VFB=0V,	R6=24kΩ	630	700	770	kHz
DTC_duty	DTC Maximum Duty Cycle	R6=24kΩ, R5=1	100kΩ	62	72	82	%
Maxduty	Oscillator Maximum Duty Cycle	V _{FB} =0V		85	90	95	%
t ss	Soft-start Time		3.5	10	16	ms	
IDLY	DELAY Pin Charge Current	VDELAY=0.8V, VFE	3=0V	2	4	6	μA
VDLY	DELAY Pin Detector Threshold Voltage	V _{FB} =0V	0.95	1.0	1.05	V	
Ron	Lx ON Resistance				0.2		Ω
ILXLIM	Lx Limit Current			2.0	3.0	3.7	Α
V _{OVP1}	OVP Detector Threshold Voltage	Vout rising			21	23	V
V _{OVP2}	OVP Release Voltage	Vουτ falling		18	Vovp1 -1		V
Vsell	SEL "L" Input Voltage	VIN_DC=2.2V				0.4	V
Vselh	SEL "H" Input Voltage	VIN_DC=5.5V		1.5			V
LDO				•	•		
Vo_ldo	LDO Output Voltage	VIN_DC= VO_LDO +	1.0V, lo_ldo=1mA	x 0.99		x 1.01	V
V _{DIF}	Dropout Voltage	Io_LDO=250mA			600 400	700 500	mV mV
ΔVo_ldo /ΔVin	Line Regulation	Io_ldo=30mA, Vo_ldo+0.5V≤Vin			0.2	%/V	
ΔVo_ldo /Δlout	Load Regulation	Vin_dc= Vo_ldo + 1mA≤lo_ldo≤250			0.4	mV /mA	
RR	Ripple Rejection	f=1kHz, Ripple I 0.2 Vp-p, Io_LDO=			65		dB
		11/ =		1	1		

LIM_LDO

Isc_ldo

VIN_DC= VO_LDO +1.0V

VIN_DC= VO_LDO +1.0V

350

70

mΑ

 $\mathsf{m}\mathsf{A}$

R1293K

NO.EA-301-160107

 V_{IN_DC} =3.6V, Ta = 25°C unless otherwise noted.

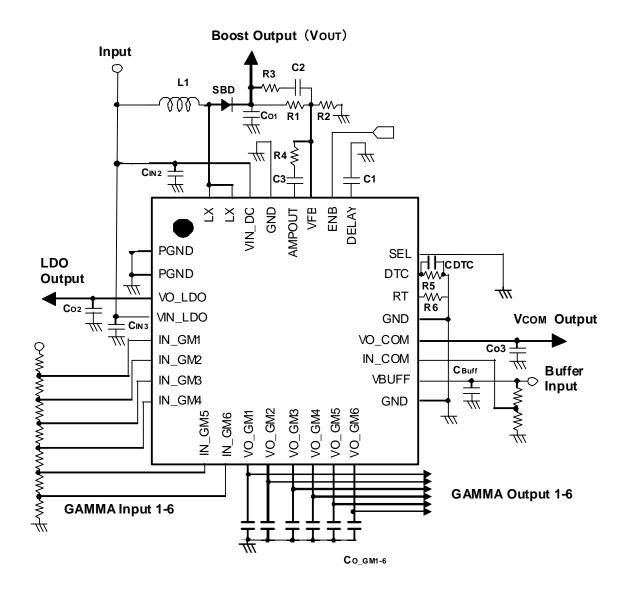
R1293K Electrical Characteristics

	lectrical Characteristics	Conditions	NA:	T	Merr	I Ira !4
Symbol	Item	Conditions	Min.	Тур.	Max.	Unit
BUFFER A		I	1	ı	1	T
V _{BUFF}	Amplifier Power Source Voltage		5		16	V
IDD_BUFF	Amplifier Supply Current	V _{BUFF} =16V, V _I =8V, VCOM 1ch + GAMMA 1 to 6ch		0.6		mA
Vos	Offset Voltage	Vi=VBUFF / 2		1		mV
Vсм_сом	VCOM Common-mode Input Voltage Range	VCOM ch	1.5		V _{BUFF} -1.5	V
Vcм_gм	GAMMA Common-mode Input Voltage Range	GAMMA ch	0		VBUFF	V
Іо_сом	VCOM Output Current	VBUFF=10V, Vi=5V	-100		100	mA
І о_gм	GAMMA Output Current	VBUFF=10V, Vi=5V	-10		10	mA
ΔV о_сом/ ΔI оит	VCOM Load Regulation	V _{BUFF} =10V, Vi=5V, -50mA≤l _{ouт} ≤+50mA		0.5	1	mV /mA
Δ V o_gm/ Δ l out	GAMMA Load Regulation	V _{BUFF} =10V, Vi=5V, -10mA≤l _{ouт} ≤+10mA		0.5	1	mV /mA
CMRR	Input Voltage Ripple Rejection	f=0.1kHz, V _{BUFF} =10V, Vi=5V, Ripple Rejection 50mVp-p		75		dB
PSRR	Power Source Ripple Rejection	f=0.1kHz, VBUFF=10V, Vi=5V, Ripple Rejection 0.2Vp-p		70		dB
Vol_com	VCOM "L" Output Voltage	V _{BUFF} =10V, V _I =1.5V, I _O =+50mA		1.5	1.55	V
		VBUFF=10V, VI=0V, Io=+5mA		0.1	0.2	V
Vol_gm	GAMMA "L" Output Voltage	V _{BUFF} =10V, V _I =0.2V, I _O =+10mA		0.2	0.25	V
		V _{BUFF} =10V, V _I =1.5V, I _O =+10mA		1.5	1.55	V
Vон_сом	VCOM "H" Output Voltage	V _{BUFF} =10V, V _I =8.5V, I _O =-50mA	8.45	8.5		V
		VBUFF=10V, VI=10V, Io=-5mA	9.8	9.9		V
Vон_gм	GAMMA "H" Output Voltage	V _{BUFF} =10V, V _I =9.8V, I _O =-10mA	9.75	9.8		V
		V _{BUFF} =10V, V _I =8.5V, I _O =-10mA	8.45	8.5		V
CONTRO	_					
VENBL	ENB "L" Input Voltage	V _{IN_DC} =2.2V			0.4	V
VENBH	ENB "H" Input Voltage	Vin_dc=5.5V	1.5			V
TTSD	Thermal Shutdown Temperature	Junction Temperature		150		٥С
T _{TSR}	Thermal Shutdown Released Temperature	Junction Temperature		100		°C

All test items listed under *Electrical Characteristics* are done under the pulse load condition (Tj≈Ta=25°C) except Opened-loop Voltage Gain (DC/ DC), Single Gain-bandwidth Range (DC/ DC), Ripple Rejection (LDO), Input Voltage Ripple Rejection (Buffer AMP) and Power Source Ripple Rejection (Buffer AMP).

^{*1} VSET=Set Output Voltage

TYPICAL APPLICATION



R1293K Typical Application

R1293K

NO.EA-301-160107

External Parts Example

Vout [V]	Frequency [kHz]	L1	CIN2	CO1	VO_GM [pF]
8~10	300	VLF5014S-4R7M1R7	C1608JB0J106M	GRM21BB31E475KA75B	1000
10~12	300	VLF5014S-4R7M1R7	C1608JB0J106M	GRM21BB31E475KA75B * 2	1000
12~16	300	NR6020T4R7N	C1608JB0J106M	GRM21BB31E475KA75B * 2	1000
8~10	700	NR4018T4R7M	GRM21BB31E475KA75B	GRM21BB31E475KA75B	1000
10~12	700	NR4018T4R7M	GRM21BB31E475KA75B	GRM21BB31E475KA75B * 2	1000
12~16	700	VLF5014S-4R7M1R7	GRM21BB31E475KA75B	GRM21BB31E475KA75B * 2	1000
8~10	1000	NR4018T4R7M	GRM21BB31E475KA75B	GRM21BB31E475KA75B	1000
10~12	1000	NR4018T4R7M	GRM21BB31E475KA75B	GRM21BB31E475KA75B * 2	1000
12~16	1000	VLF5014S-4R7M1R7	GRM21BB31E475KA75B	GRM21BB31E475KA75B * 2	1000

Vout	Frequency	CO3	CIN3	CO2
[V]	[kHz]			
8~10	300	TMK316BJ106MD-TD	CM105B105K10AT	CM105B105K10AT
10~12	300	TMK316BJ106MD-TD	CM105B105K10AT	CM105B105K10AT
12~16	300	TMK316BJ106MD-TD	CM105B105K10AT	CM105B105K10AT
8~10	700	TMK316BJ106MD-TD	CM105B105K10AT	CM105B105K10AT
10~12	700	TMK316BJ106MD-TD	CM105B105K10AT	CM105B105K10AT
12~16	700	TMK316BJ106MD-TD	CM105B105K10AT	CM105B105K10AT
8~10	1000	TMK316BJ106MD-TD	CM105B105K10AT	CM105B105K10AT
10~12	1000	TMK316BJ106MD-TD	CM105B105K10AT	CM105B105K10AT
12~16	1000	TMK316BJ106MD-TD	CM105B105K10AT	CM105B105K10AT

Vout	Frequency	R4	C3	R3	C2	R1	R2	R6	R5	CDTC	C1
[V]	[kHz]	[kΩ]	[pF]	[kΩ]	[pF]	[kΩ]	[kΩ]	[kΩ]	[kΩ]	[uF]	[uF]
8~10	300	3.3	1000	8.2	120	(VOUT-1) * R2	33	62	330	-	0.22
10~12	300	3.3	1000	8.2	120	(VOUT-1) * R2	33	62	330	-	0.22
12~16	300	4.7	1500	10	47	(VOUT-1) * R2	22	62	330	-	0.22
8~10	700	3.3	1000	8.2	120	(VOUT-1) * R2	33	24	130	-	0.22
10~12	700	3.3	1000	8.2	120	(VOUT-1) * R2	33	24	130	-	0.22
12~16	700	4.7	1500	10	47	(VOUT-1) * R2	22	24	130	-	0.22
8~10	1000	3.3	1000	8.2	120	(VOUT-1) * R2	33	16	91	-	0.22
10~12	1000	3.3	1000	8.2	120	(VOUT-1) * R2	33	16	91	-	0.22
12~16	1000	4.7	1500	10	47	(VOUT-1) * R2	22	16	91	-	0.22

TECHNICAL NOTES

Output Voltage Setting (DC/DC)

Vout controls the VFB pin voltage to maintain VFB=1.0V. Vout can be set using R1 and R2 in the following equation. Vout voltage should be set between 5V to 16V. Also, the sum of R1 and R2 should be equal or less than $500k\Omega$.

 $V_{OUT} = V_{FB} x (R1 + R2) / R2$

Phase Compensation Setting (DC/ DC)

A 180 degree phase shift may be caused by the inductor (L1) and the capacitor (C_{01}). The phase shift reduces phase margin and stability of the system. Thus, it is necessary to keep a leading phase margin. In the following equation, the pole is made by L1 and C_{01} .

Fpole ~ 1 / $\{2 \times \pi \times \sqrt{(L1 \times C_{01})}\}$

The phase compensation and the system gain can be set by using R4, C3 and C2. Please refer to *Typical Application* (P.10,11) for positioning and setting value examples. In the following equation, the zero is made by R4 and C3.

Fzero $\sim 1 / (2 \times \pi \times R4 \times C3)$

When selecting the values for R4 and C3, please consider that the cutoff frequency of zero should be approximately equal to the cutoff frequency of pole.

For example, if L1=10 μ H and C₀₁=10 μ F, the cutoff frequency of pole is approximately 16kHz.

The gain can be set by the resistance ratio of R4 and RT which is the combined resistance of R1 and R2 (RT=R1xR2/(R1+R2)). If R4 is larger than RT, the gain becomes high. The high gain improves the response characteristic; however, the extremely high gain decreases stability of the operation. It is important to select an appropriate value for R4. In the following equation, zero is made by R1 and C2.

Fzero $\sim 1/(2 \times \pi \times R1 \times C2)$

Set the cutoff frequency of zero lower than the cutoff frequency of pole.

Reduction of Feedback Voltage Noise (DC/ DC)

If the system noise is large, it may wrap around the V_{FB} pin and causes unstable operation. In this case, set R1 and R2 resistance values lower to reduce the noise entering the V_{FB} pin. Or, place R3 with $1k\Omega$ to $5k\Omega$ to reduce the noise entering the V_{FB} pin as shown in *Typical Application* (P.10,11).

Input Voltage Setting (DC/ DC and LDO)

The input voltage ranges of the V_{IN_DC} and V_{IN_LDO} pins are from 2.2V to 5.5V. Place a bypass capacitor between V_{IN} and GND. Use Boost Output as the input voltage for the V_{BUFF} pin.

R1293K

NO.EA-301-160107

Oscillator Frequency Setting (DC/ DC)

By connecting R6 to the the RT pin, fosc can be set in the range of 300kHz to 1MHz. R6 can be calculated by inserting a desired oscillator frequency value into fosc in the following equation.

 $R6 = 19.128 \times 10^{9} / Fosc - 3443$

Example: Oscillator Frequency 700kHz

 $R6 = 19.128 \times 10^{9} / (700 \times 10^{3}) - 3443 = 23883 \approx 24k\Omega$

Maxduty and Maxduty Soft-start Adjustment (DC/ DC)

Maxduty is preset to 90% (Typ.); however, it can be set lower by adding R5 to the DTC pin. Maxduty is determined by R6 and R5 as shown in the equation below. The preset Maxduty is compared with the Maxduty set by the DTC pin, and the lower Maxduty will be selected.

Maxduty (DC) =
$$\frac{0.3267 \times R5 - 0.6285 \times R6 + 2367}{R6 + 3550}$$

Example: R6=24k Ω , R5=110k Ω

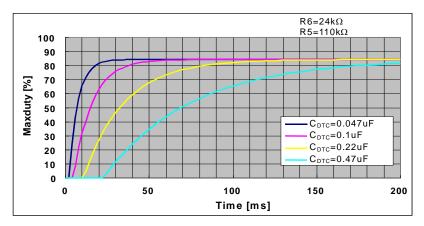
 $Maxduty = (0.3267 \times 110000 - 0.6285 \times 24000 + 2367) / 24000 + 3550)$

≈ 0.843 **→** 84.3%

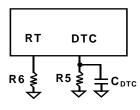
By adding C_{DTC} to the DTC pin, Maxduty can increase gradually and the inrush current can be controlled. (Maxduty Soft-start). After start-up, Maxduty after t-time (Maxduty (t)) can be calculated by the following equation.

Maxduty (t) =
$$\frac{0.3267 \times R5 \times [1 - EXP(-t / C_{DTC} \times R5)] - 0.6285 \times R6 + 2367}{R6 + 3550}$$

Example: R6=24k Ω , R5=110k Ω , C_{DTC}=0.047 μ F to 0.47 μ F



Typical Application with RT Pin/ DTC Pin



When using Maxduty soft-start, it is recommended that latch protection delay time (t_{DLY}) be set $t_{DLY} > 6$ x (R5 x C_{DTC}). t_{DLY} should be longer than the soft-start time.

Overcurrent Protection (DC/DC)

The overcurrent protection circuit monitors the Nch-swich current and immediately turns off if the Nch-switch current reaches the current limit. Nch-switch turns on every internal reference clock cycle and turns off if the Nch-switch current reaches the current limit again.

Short Current Protection/ Protection Delay Time Setting (DC/ DC)

If Boost Output drops and causes the VFB voltage drop to 85% of the preset value, the IC recognizes a short-circuit and starts to charge C1. If the short-circuit condition persists for a certain period of time and the DELAY pin voltage rechaes V_{DLY}, the latch-type protection circuit shuts down Boost Output. t_{DLY} can be set by C1 shown in the following equations.

 $t_{\text{DLY}} = C \ x \ V_{\text{DLY}} \ / \ I_{\text{DLY}}$

To release latch state, make V_{N,DC} voltage below the UVLO detector threshold and then restart, or set ENB "H" once and then set it back to "L".

Undervoltage Lock Out (DC/ DC)

If the $V_{\text{\tiny NLDC}}$ pin voltage becomes equal or lower than UVLO detector threshold, the UVLO circuit immediately disables the switching output.

Thermal Shutdown (LDO and Buffer AMP)

Thermal shutdown circuit detects overheating of the IC and turns off VCOM Output, GAMMA Output, and LDO Outputs to reset the IC if the junction temperature becomes more than the detector threshold. If the causes of overheating are removed and the junction temperature decreases to the release temperature, the IC restarts.

Standby Mode (DC/ DC and Buffer AMP)

By setting the ENB pin "H", DC/ DC and Buffer AMP go into Standby mode and the output shuts down. LDO is always-on and outputs voltage.

SEL Pin Mode Switching (DC/DC)

By setting the SEL pin voltage "L", the switching speed of a built-in MOSFET shifts to moderate mode to reduce the influences of noise to external parts. The SEL pin voltage operates in normal mode when "H".

Diode, Inductor and Capacitor Selections (DC/ DC, LDO and Buffer AMP)

Efficiency and stability of system can be affected by the following conditions. Spike voltage may be generated by the influence of an inductor when Nch MOSFET turns off. Therefore, diodes, inductors and capacitors should not exceed the voltage tolerance of the capacitor connected to V_{OUT} or their respected rated values (voltage, current and power). Please refer to *Operation of DC/ DC Converter and Output Current* (P.15). Choose the diode with low forward voltage (schottky diode), small reverse current and fast switching speed.

Operation of DC/ DC Converter and Output Current

Figure 1. Basic Circuit

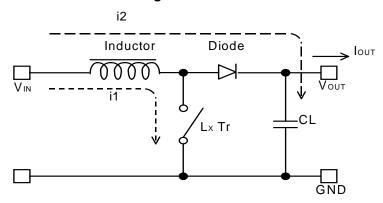
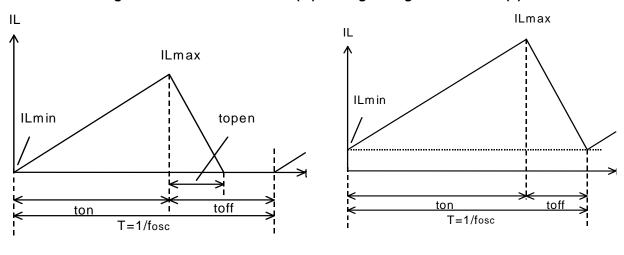


Figure 2. The inductor current (IL) flowing through the inductor (L)



Discontinuous Mode

Continuous Mode

There are two operation modes in the PWM step-up DC/ DC converter: continuous mode and discontinuous mode. When a transistor is in the On-state, the voltage to be applied to L is described as V_{IN} . An increase in the inductor current (i1) can be written as follows:

Δi1 = V_{IN} × ton / L Formula 1

In the step-up circuit, the energy accumulated during the On-state is transferred into the capacitor even in the Off-state. A decrease in the inductor current (i2) can be written as follows:

∆i2 = (Vout − Vin) × topen / L..... Formula 2

In the PWM switching control, i1 and i2 become continuous when topen=toff, which is called continuous mode.

When the IC is in the continuous mode and operates in steady-state conditions, the variations of i1 and i2 are same:

 $V_{IN} \times ton / L = (V_{OUT} - V_{IN}) \times toff / L$ Formula 3

Therefore, the duty cycle in the continuous mode is:

Duty = ton / (ton + toff) = $(V_{OUT} - V_{IN}) / V_{OUT}$Formula 4

When topen=toff, the average of IL is:

IL (Ave.) = V_{IN} × ton / (2 × L) Formula 5

If the input voltage (V_{IN}) is equal to V_{OUT} , the output current (I_{OUT}) is:

 $lout = V_{IN}^2 \times ton / (2 \times L \times V_{OUT})$ Formula 6

If I_{OUT} is larger than Formula 6, the IC switches to the continuous mode.

ILmax flowing through L is:

 $IL_{max} = I_{OUT} \times V_{OUT} / V_{IN} \times ton / (2 \times L)$ Formula 7

ILmax = Iout x Vout / Vin + Vinx T x (Vout - Vin) / (2 x L x Vout) ······ Formula 8

As a result, ILmax becomes larger compared to I_{OUT}.

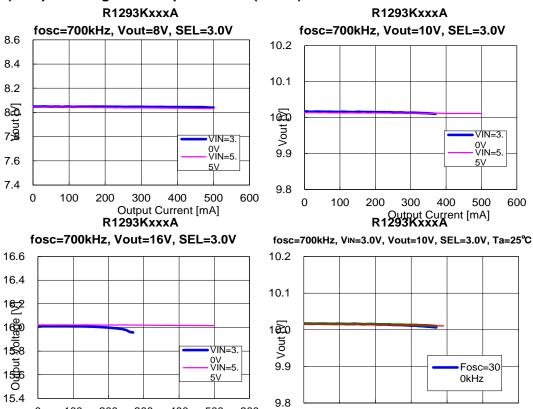
When considering the input and output conditions or selecting the external parts, please pay attention to ILmax.

The above calculations are based on the ideal operation of the ICs in the continuous mode. They do not include the losses caused by the external parts or L_X switch. The actual maximum output current will be 50% to 80% of the above calculation results. Especially, if IL is large or V_{IN} is low, it may cause the switching losses. As for V_{OUT} , please consider V_F of the diode (approximately 0.8V).

TYPICAL CHARACTERISTICS

 $V_{IN} = V_{IN_DC} = V_{IN_LDO}$, unless otherwise noted.

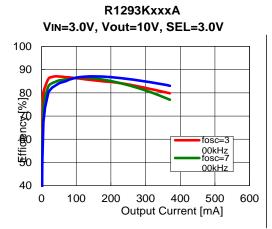
1) Output Voltage vs. Output Current (DCDC)

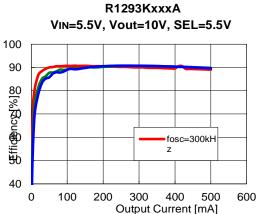


Output Current [mA]

2) Efficiency vs. Output Current (DCDC)

Output Current [mA]

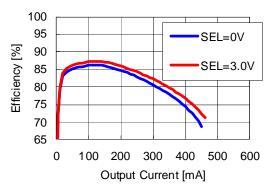




R1293KxxxA V_{IN}=3.0V, SEL=3.0V, Ta=25℃ 100 90 80 Efficiency [%] 70 60 osc=300kHz,Vout=8V fosc=700kHz,Vout=8V 50 osc=1 MHz.Vout=8 V 40 fosc=300kHz,Vout=16V 30 fosc=700kHz,Vout=16V 20 fosc=1 MHz,Vout=1 6V 0 100 200 300 400 500 600 Output Current [mA]

R1293KxxxA V_{IN}=5.5V, SEL=5.5V, Ta=25℃ 100 90 80 Efficiency [%] 70 fosc=300kHz,Vout=8V 60 fosc=700kHz,Vout=8V 50 fosc=1MHz,Vout=8V 40 fosc=300kHz.Vout=16V fosc=700kHz,Vout=16V 30 fosc=1MHz,Vout=16V 20 100 0 200 300 400 500 600 Output Current [mA]

R1293KxxxA fosc=700kHz,Vin=3.0V, Vout=10V, Ta=25°C



3) Output Voltage Waveform (DCDC)

R1293KxxxA

fosc=700kHz, Vin=3.0V, Vout=10V, Ta=25°C

SEL=0V, lout=80mA

Tek (#]

CH1=Vout
CH2=Lx

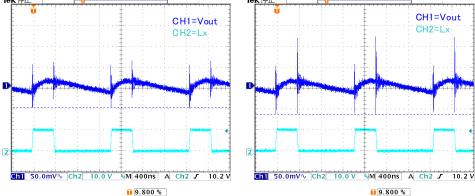
R1293KxxxA

F1293KxxxA

fosc=700kHz, Vin=3.0V, Vout=10V, Ta=25°C

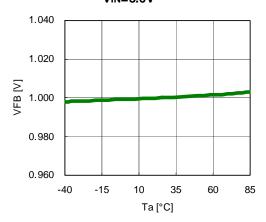
SEL=3.0V, lout=80mA

CH1=Vout
CH2=Lx



4) VFB Voltage vs. Temperature R1293KxxxA

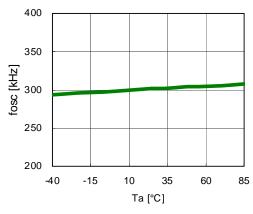
VIN=3.6V



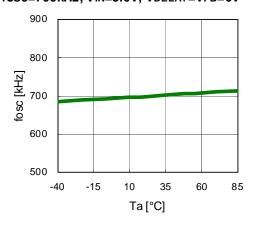
5) Oscillator Frequency vs. Temperature

R1293KxxxA

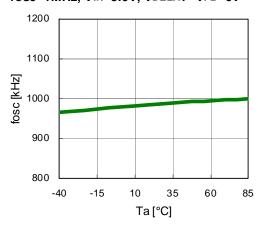
fosc=300kHz, VIN=3.6V, VDELAY=VFB=0V



R1293KxxxA fosc=700kHz, Vin=3.6V, VdeLay=Vfb=0V

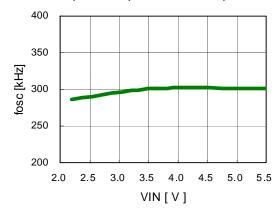


R1293KxxxA fosc=1MHz, Vin=3.6V, VDELAY=VFB=0V

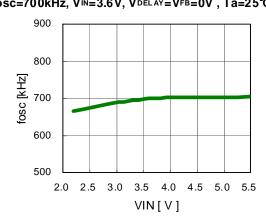


6) Oscillator Frequency vs. VIN Voltage R1293KxxxA

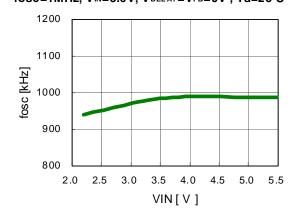
fosc=300kHz, VIN=3.6V, VDELAY=VFB=0V , Ta=25°C fosc=700kHz, VIN=3.6V, VDELAY=VFB=0V , Ta=25°C



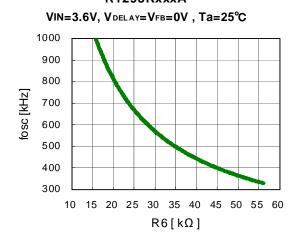
R1293KxxxA



 $R1293KxxxA \\ fosc=1MHz, Vin=3.6V, Vdelay=Vfb=0V, Ta=25^{\circ}C$

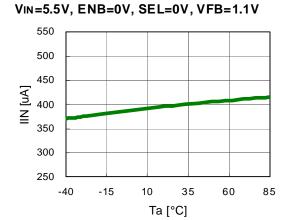


7) Oscillator Frequency vs. R6 Resistance R1293KxxxA



8) Standby VIN Current vs. Temperature 9) Supply VIN Current vs. Temperature R1293KxxxA R1293KxxxA

VIN=ENB=5.5V 90 80 70 ISTB [uA] 60 50 40 30 -40 -15 10 35 60 85 Ta [°C]



10) UVLO Detector Threshold vs. Temperature 11) UVLO Released Voltage vs. Temperature R1293KxxxA R1293KxxxA

VIN=2.2V → 1.7V

2.00

1.95

1.90

1.85

1.80

-40

-15

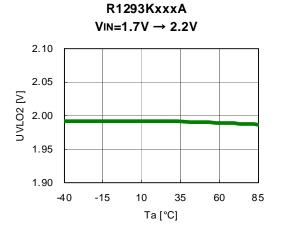
10

35

60

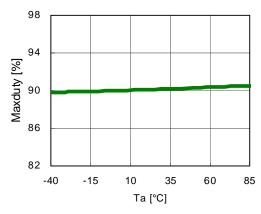
85

Ta [°C]



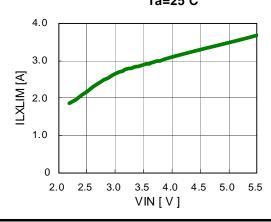
12) Oscillator Maximum Duty Cycle vs. Temperature R1293KxxxA

VIN=3.6V, VFB=0V



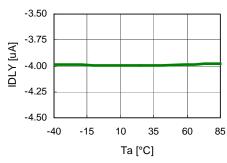
13) LX Limit Current vs. VIN Voltage

R1293KxxxA Ta=25℃



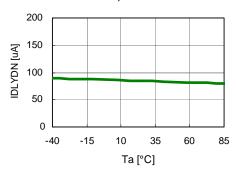
14) DELAY Pin Charge Current vs. Temperature

R1293KxxxA VIN=3.6V, VDELAY=0.8V, VFB=0V



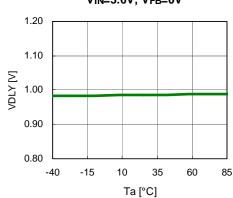
15) DELAY Pin Discharge Current vs. Temperature

R1293KxxxA VIN=3.6V, VDELAY=0.1V



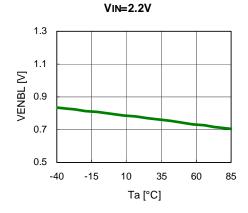
16) DELAY Pin Detector Threshold Voltage vs. Temperature

R1293KxxxA VIN=3.6V, VFB=0V



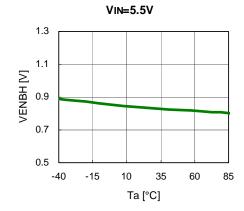
17) ENB "L" Input Voltage vs. Temperature

R1293KxxxA



18) ENB "H" Input Voltage vs. Temperature

R1293KxxxA



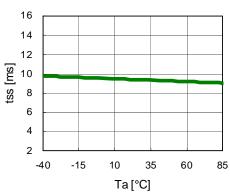
19) DTC Maximum Duty Cycle vs. Temperature 20) DTC Maximum Duty Cycle vs. R5/R6 R1293KxxxA R1293KxxxA

R6=24k Ω , R5=100k Ω 85 80 DTC_duty [%] 75 70 65 60 -15 10 35 60 85 -40 Ta [°C]

VIN=3.6V, R6=24k Ω , Ta=25°C 100 80 DTC_duty [%] 60 40 20 0 1.00 2.00 4.00 5.00 6.00 R5/R6

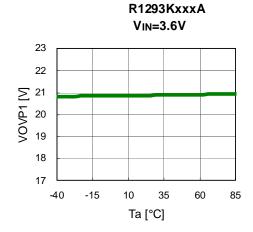
21) Soft Start Time vs. Temperature R1293KxxxA

VIN=3.6V

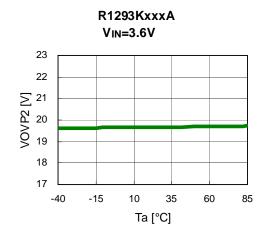


85

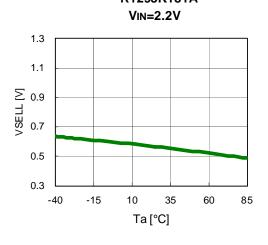
22) OVP Detector Threshold Voltage vs Temperature

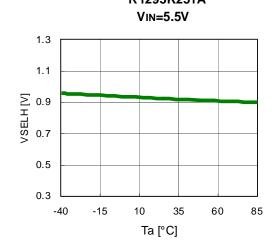


23) OVP Release Voltage vs Temperature

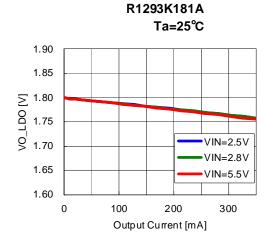


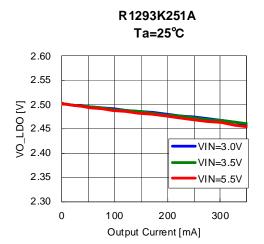
24) SEL "L" Input Voltage vs. Temperature 25) SEL "H" Input Voltage vs. Temperature R1293K181A R1293K251A

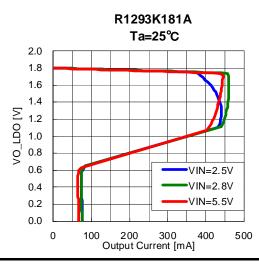


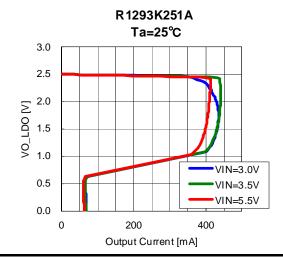


26) Output Voltage vs Output Current (LDO)

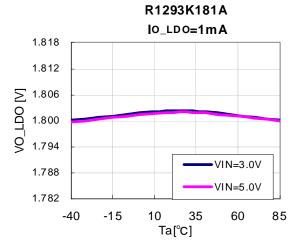


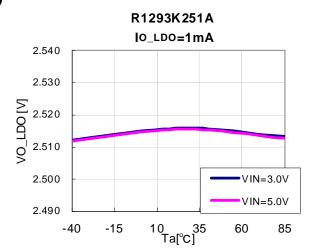




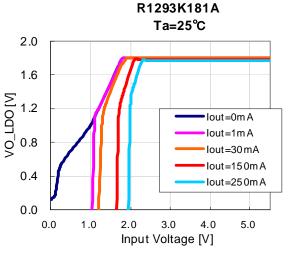


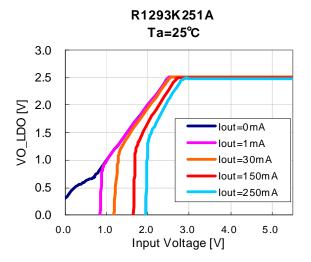
27) Output Voltage vs. Temperature (LDO)



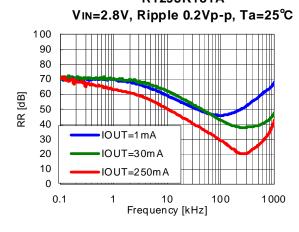


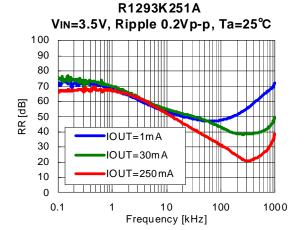
28) Output Voltage vs. VIN Voltage (LDO)





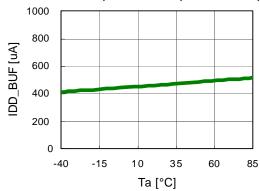
29) LDO Ripple Rejection vs. Frequency R1293K181A





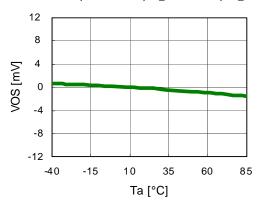
30) Amplifier Supply Current vs. Temperature (BUFFER AMP) R1293KxxxA

VIN=3.6V, VBUFF=16V, IN_COM=8V, IN_GM*=8V



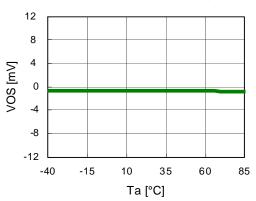
31) VCOM Offset Voltage vs. Temperature R1293KxxxA

VIN=3.6V, VBUFF=7V, IN_COM=3.5V, IO_COM=0m A



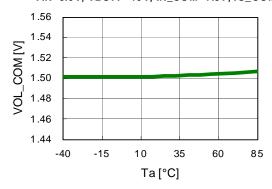
32) GAMMA Offset Voltage vs. Temperature R1293KxxxA

VIN=3.6V, VBUFF=7V, IN_GM*=3.5V, IO_GM*=0mA

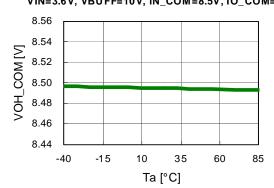


33) VCOM Output Voltage vs. Temperature R1293KxxxA

VIN=3.6 V, VBU FF=10 V, IN_COM=1.5 V, IO_COM=+50 mA

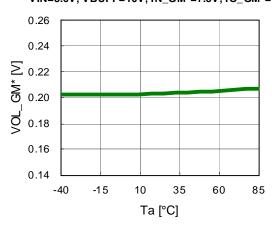


R1293K xxxA VIN=3.6V, VBUFF=10V, IN_COM=8.5V, IO_COM=-50mA



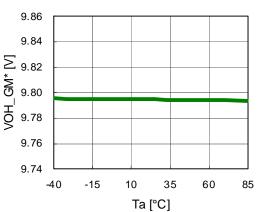
34) GAMMA Output Voltage vs. Temperature

R1293KxxxA



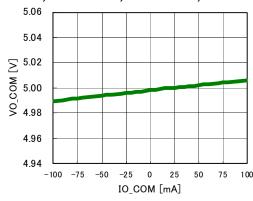
R1293KxxxA



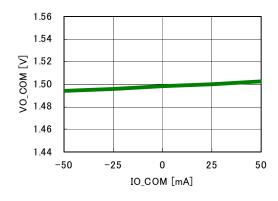


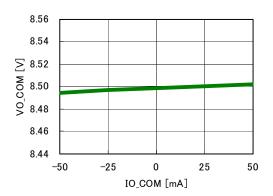
35) VCOM Output Voltage vs. Output Current R1293KxxxA

VIN=3.6V, VBUFF=10V, IN_COM=5V, Ta=25°C



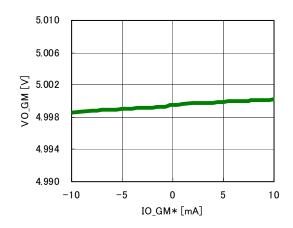
R1293KxxxA R1293KxxxA VIN=3.6V, VBUFF=10V, IN_COM=1.5V, Ta=25°C VIN_DC=3.6V, VBUFF=10V, IN_COM=8.5V, Ta=25°C



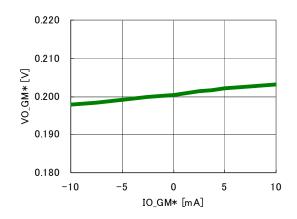


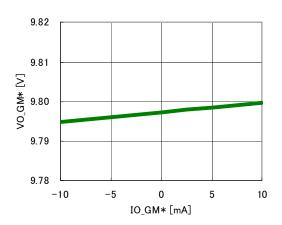
36) GAMMA Output Voltage vs. Output Current R1293KxxxA

VIN=3.6V, VBUFF=10V, IN_GM*=5V, Ta=25°C



R1293KxxxA R1293KxxxA VIN=3.6V, VBUFF=10V, IN_GM*=0.2V, Ta=25°C VIN=3.6V, VBUFF=10V, IN_GM*=9.8V, Ta=25°C

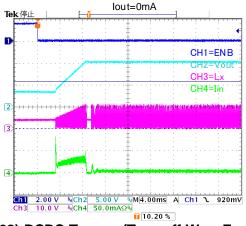


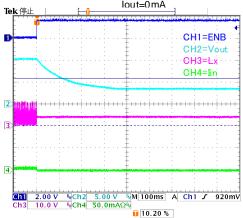


37) DCDC Turn-on/Turn-off WaveForm by ENB R1293KxxxA

R1293KxxxA

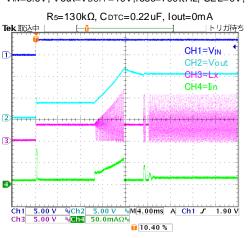
Vin=3.6V, Vout=Vbuff=10V,fosc=700kHz, SEL=0V, Ta=25°C Vin=3.6V, Vout=Vbuff=10V,fosc=700kHz, SEL=0V, Ta=25°C

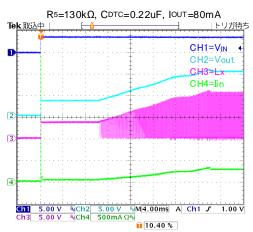




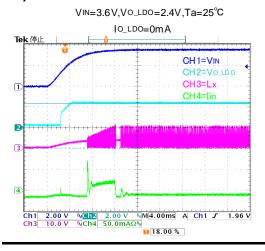
38) DCDC Turn-on/Turn-off WaveForm (DTC Soft Start) by VIN R1293KxxxA R1293KxxxA

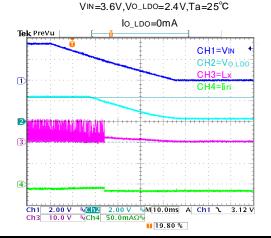
VIN=3.6V, Vout=VBUFF=10V,fosc=700kHz, SEL=0V, Ta=25°C VIN=3.6V, Vout=VBUFF=10V, Ta=25°C VIN=3.6V, Ta=25°





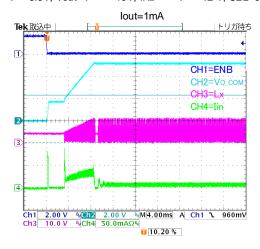
39) LDO Turn-on/Turn-off WaveForm by VIN

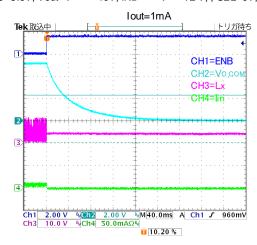




40) VCOM Turn-on/Turn-off WaveForm by ENB

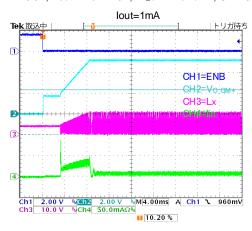
VIN=3.6V, Vout=VBUFF=10V, IN_COM=VBUFF/2 V, SEL=0V, Ta=25°C S. Vout=VBUFF=10V, IN_COM=VBUFF=10V, IN_COM=VBUFF

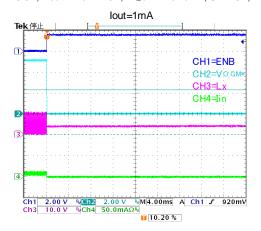




41) GAMMA Turn-on/Turn-off WaveForm by ENB

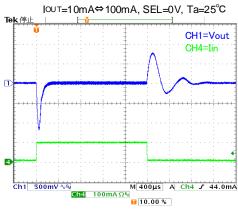
 $V_{\text{IN}=3.6V, \ Vout=VBUFF=10V, \ IN_GM=VBUFF/2\ V, \ SEL=0V, \ Ta=25\% CM=3.6V, \ Vout=VBUFF=10V, \ IN_GM=VBUFF/2\ V, \ SEL=0V, \ Ta=25\% CM=3.6V, \ Vout=VBUFF=10V, \ IN_GM=VBUFF/2\ V, \ SEL=0V, \ Ta=25\% CM=3.6V, \ Vout=VBUFF=10V, \ IN_GM=VBUFF/2\ V, \ SEL=0V, \ Ta=25\% CM=3.6V, \ Vout=VBUFF=10V, \ IN_GM=VBUFF/2\ V, \ SEL=0V, \ Ta=25\% CM=3.6V, \ Vout=VBUFF=10V, \ IN_GM=VBUFF/2\ V, \ SEL=0V, \ Ta=25\% CM=3.6V, \ Vout=VBUFF=10V, \ IN_GM=VBUFF/2\ V, \ SEL=0V, \ Ta=25\% CM=3.6V, \ Vout=VBUFF=10V, \ IN_GM=VBUFF/2\ V, \ SEL=0V, \ Ta=25\% CM=3.6V, \ Vout=VBUFF=10V, \ IN_GM=VBUFF/2\ V, \ SEL=0V, \ Ta=25\% CM=3.6V, \ Vout=VBUFF=10V, \ IN_GM=VBUFF/2\ V, \ SEL=0V, \ Ta=25\% CM=3.6V, \ Vout=VBUFF=10V, \ IN_GM=VBUFF/2\ V, \ SEL=0V, \ Ta=25\% CM=3.6V, \ Vout=VBUFF=10V, \ IN_GM=VBUFF/2\ V, \ SEL=0V, \ Ta=25\% CM=3.6V, \ Vout=VBUFF=10V, \ IN_GM=VBUFF/2\ V, \ SEL=0V, \ Ta=25\% CM=3.6V, \ Vout=VBUFF/2\ V, \ SEL=0V, \ Ta=25\% CM=3.0V, \ Ta=2$

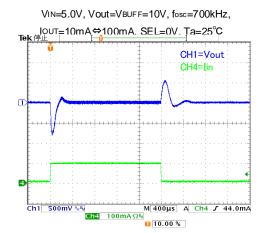




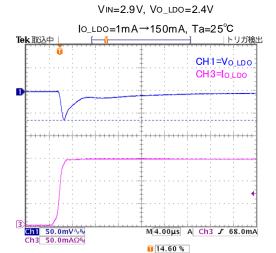
42) DCDC Load Tranjent Response

VIN=3.3V, Vout=VBUFF=10V, fosc=700kHz,

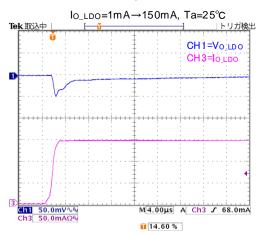




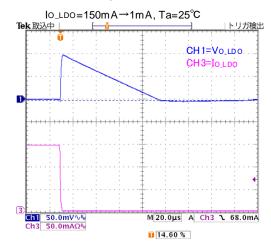
43) LDO Load Tranjent Response



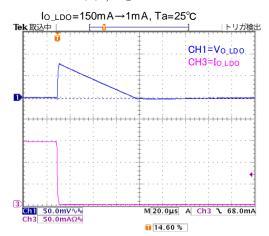
VIN=5.5V, $VO_LDO=2.4V$



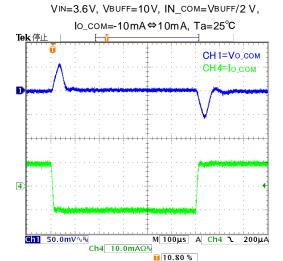
VIN=2.9V, VO_LDO=2.4V



VIN=5.5V, $VO_LDO=2.4V$

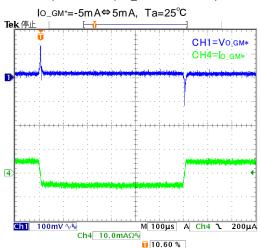


44) VCOM Load Tranjent Response



45) GAMMA Load Tranjent Response

VIN=3.6V, VBUFF=10V, IN_GM*=VBUFF/2 V,





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